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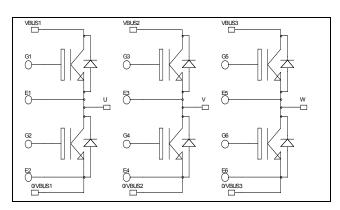
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APTGF90TA60PG

Triple phase leg NPT IGBT Power Module



VBUS1 VBUS2 VBUS3 • G1 • G3 • G5 • E1 • E3 • E5 • 0/VBUS1 0/VBUS2 0/VBUS3 • E2 • E4 • E6 • G2 • G4 • G6 • U V W

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		600	V
т	Continuous Collector Current	$T_c = 25^{\circ}C$	110	
I _C	Continuous Collector Current	$T_c = 80^{\circ}C$	90	А
I _{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	315	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_c = 25^{\circ}C$	416	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	200A @ 600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

$V_{CES} = 600V$ $I_{C} = 90A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
 - High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a phase leg of three times the current capability
- Module can be configured as a three phase bridge
- Module can be configured as a boost followed by a full bridge
- RoHS compliant

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit	
т	Zara Gata Valtaga Collactor Current	$V_{GE} = 0V$	$T_i = 25^{\circ}C$			250	۸	
I _{CES}	Zero Gate Voltage Collector Current	$V_{CE} = 600V$	$T_{i} = 125^{\circ}C$			500	μA	
V _{CE(sat)}	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		2.0	2.5	V	
		$I_C = 90A$	$T_j = 125^{\circ}C$		2.2		v	
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$		3		5	V	
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20 V, V_{CE} = 0V$				±150	nA	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			4300		
C _{oes}	Output Capacitance				470		pF
Cres	Reverse Transfer Capacitance				400		
Qg	Total gate Charge	$V_{GE} = 15V$			330		nC
Q _{ge}	Gate – Emitter Charge	$V_{Bus} = 300V$			290		
Q _{gc}	Gate – Collector Charge	$I_{\rm C} = 90 {\rm A}$		200			
T _{d(on)}	Turn-on Delay Time	Inductive Switch		26		ns	
T _r	Rise Time	$V_{GE} = 15V$		25			
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 400V$ $I_C = 90A$		150			
T _f	Fall Time	$R_G = 5 \Omega$		30			
T _{d(on)}	Turn-on Delay Time	Inductive Switch		26		ns	
T _r	Rise Time	$V_{GE} = 15V$ $V_{Bus} = 400V$ $I_{C} = 90A$ $R_{G} = 5 \Omega$			25		
T _{d(off)}	Turn-off Delay Time				170		
T _f	Fall Time				40		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 400V$	$T_j = 125^{\circ}C$		4.3		Ŧ
E _{off}	Turn-off Switching Energy	$I_{C} = 90A$ $R_{G} = 5 \Omega$	$T_j = 125^{\circ}C$		3.5		mJ

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
т	Maximum Reverse Leakage Current	V _R =600V	$T_j = 25^{\circ}C$			250	۸
I _{RM}			$T_{j} = 125^{\circ}C$			500	μA
$I_{\rm F}$	DC Forward Current		$Tc = 70^{\circ}C$		60		А
	Diode Forward Voltage	$I_F = 60A$	$I_{\rm F} = 60 {\rm A}$		1.6	1.8	
$V_{\rm F}$		$I_{\rm F} = 120 {\rm A}$			1.9		V
		$I_F = 60A$	$T_j = 125^{\circ}C$		1.4		
t _{rr}	Reverse Recovery Time	$I_{\rm F} = 60A$ $V_{\rm R} = 400V$ $di/dt = 200A/\mu s$	$T_j = 25^{\circ}C$		130		ns
			$T_j = 125^{\circ}C$		170		115
Q _{rr}	Reverse Recovery Charge		$T_j = 25^{\circ}C$		220		nC
			$T_{j} = 125^{\circ}C$		920		ne

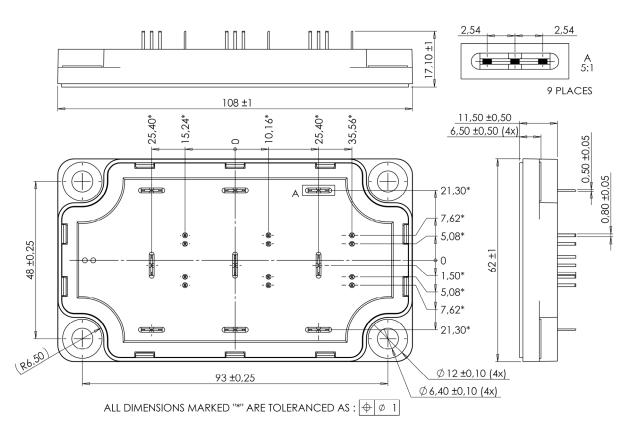


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Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Innction to Case Thermal Resistance		IGBT			0.3	- C/W
			Diode			0.9	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

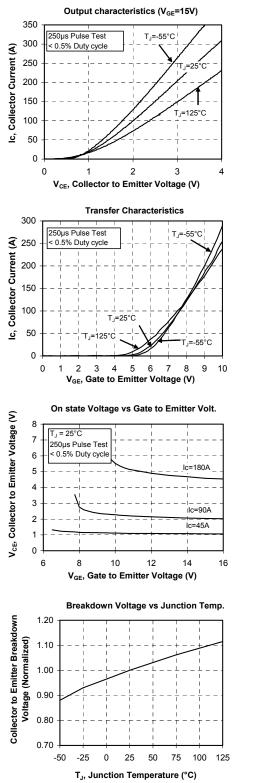
SP6-P Package outline (dimensions in mm)



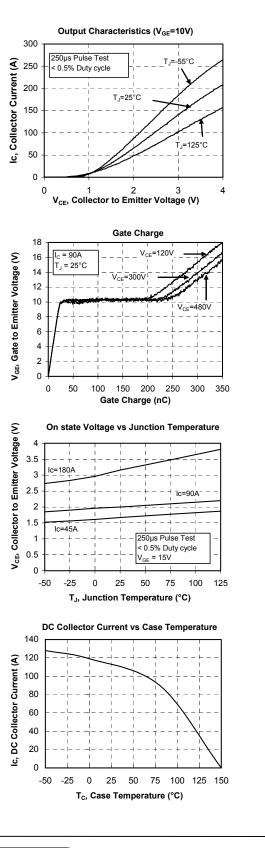
See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com



Typical Performance Curve

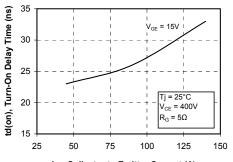


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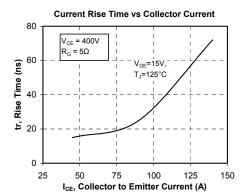




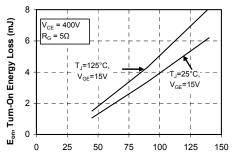
Turn-On Delay Time vs Collector Current



I_{CE}, Collector to Emitter Current (A)

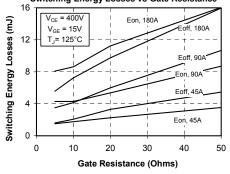






I_{CE}, Collector to Emitter Current (A)





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Turn-Off Delay Time vs Collector Current 250 (us) V_{GE}=15V, td(off), Turn-Off Delay Time T_=125°C 200 150 100 _{SE}=15V V_{CE} = 400V T_J=25°C $R_G = 5\Omega$ 50 25 100 125 150 50 75 I_{CE}, Collector to Emitter Current (A) **Current Fall Time vs Collector Current** 80 = 400V, V_{GE} = 15V, R_G = 5Ω 60 Fall Time (ns) T₁ = 125°C 40 Ŧ, 20 T_J = 25°C 0 50 75 100 125 I_{CE}, Collector to Emitter Current (A) 25 150 Turn-Off Energy Loss vs Collector Current 6 Eoff, Turn-off Energy Loss (mJ) V_{CE} = 400V 125°C 5 V_{GE} = 15V $R_{c} = 5\Omega$ 4 3 : 25°C 2 1 0 0 25 50 75 100 125 150 ICE, Collector to Emitter Current (A) Switching Energy Losses vs Junction Temp. 10 Switching Energy Losses (mJ) V_{CE} = 400 V_{GE} = 15V Eon. 180A 8 $R_G = 5\Omega$ _Eoff, 180A 6 4 .Eon. 90A Foff 90A 2 Eoff, 454 Eon, 45A 0

75

100

125

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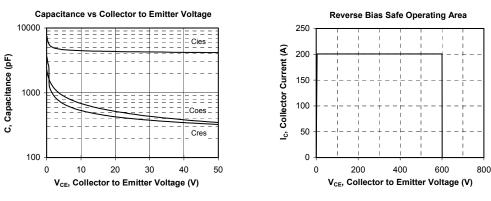
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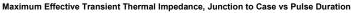
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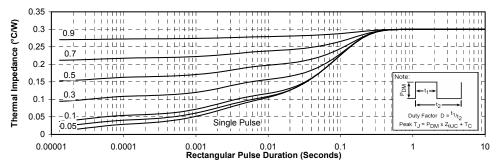
T_J, Junction Temperature (°C)

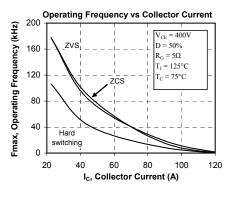


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